SN65LVDS387, SN75LVDS387, SN65LVDS389, SN75LVDS389 HIGH-SPEED DIFFERENTIAL LINE DRIVERS

SLLS362B - SEPTEMBER 1999 - REVISED NOVEMBER 1999

•	Eight ('389) or Sixteen ('387) Line Drivers
	Meet or Exceed the Requirements of ANSI
	EIA/TIA-644 Standard

- Designed for Signaling Rates up to 630 Mbps With Very Low Radiation (EMI)
- **Low-Voltage Differential Signaling With** Typical Output Voltage of 350 mV and a **100** Ω Load
- **Propagation Delay Times Less Than 2.9 ns**
- Output Skew Is Less Than 150 ps
- Part-to-Part Skew Is Less Than 1.5 ns
- 35 mW Total Power Dissipation in Each **Driver Operating at 200 MHz**
- **Driver is High Impedance When Disabled or** With $V_{CC} < 1.5 \text{ V}$
- SN65' Version Bus-Pin ESD Protection Exceeds 12 kV
- Packaged in Thin Shrink Small-Outline Package With 20-mil Terminal Pitch
- Low-Voltage TTL (LVTTL) Logic Inputs Are **5-V Tolerant**

description

The SN65LVDS389 and SN75LVDS389 are eight and the SN65LVDS387 and SN75LVDS387 are sixteen differential line drivers that implement the electrical characteristics of low-voltage differential signalling (LVDS). This signaling technique lowers the output voltage levels of 5-V differential standard levels (such as EIA/TIA-422B) to reduce the power, increase the switching speeds, and allow operation with a 3.3-V supply rail. Any of the sixteen current-mode drivers will deliver a minimum differential output voltage magnitude of 247 mV into a 100- Ω load when enabled.

DBT PACKAGE (TOP VIEW)					
			-		
V _{CC} [GND [18 19	21 20] B4Y] B4Z		

'LVDS389

(TOP VIEW)					
GND [64	l A1Y		
	1 0] A1Z		
V _{CC} [2] A2Y		
V _{CC} [3	~-	A2Z		
ENA [4		i		
A1A	5	~~	=		
A2A	6	~~;	=		
	7		_		
A3A [3] A4Z		
A4A [d ~	~~	B1Y		
ENB [10	~~;	B1Z		
B1A	11	Υ'.	B2Y		
B2A	12	~~	B2Z		
ВЗА [13	52] B3Y		
B4A	14	~ · E	B3Z		
GND [15	50	B4Y		
V _{CC}	16	49	B4Z		
V _{CC}	17	48] C1Y		
GND [18	47] C1Z		
C1A [19	46] C2Y		
C2A	20	45] C2Z		
C3A [21	44] C3Y		
C4A [22	43] C3Z		
ENC [23	42	C4Y		
D1A [24	41] C4Z		
D2A [25	40] D1Y		
D3A [26	39] D1Z		
D4A [27	38	D2Y		
END [28	37	D2Z		
GND [29	36	D3Y		
V _{CC}	30	35	D3Z		
V _{CC} [31		D4Y		
GND [32	33	D4Z		
			_		

'LVDS387 DGG PACKAGE

The intended application of this device and signaling technique is for point-to-point and multidrop baseband data transmission over controlled impedance media of approximately 100 Ω . The transmission media can be printed-circuit board traces, backplanes, or cables. The large number of drivers integrated into the same substrate, along with the low pulse skew of balanced signaling, allows extremely precise timing alignment of clock and data for synchronous parallel data transfers. When used with the companion 16- or 8-channel receivers, the SN65LVDS386 or SN65LVDS388, over 300 million data transfers per second in single-edge clocked systems are possible with very little power. (Note: The ultimate rate and distance of data transfer is dependent upon the attenuation characteristics of the media, the noise coupling to the environment, and other system characteristics.)



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SN65LVDS387, SN75LVDS387, SN65LVDS389, SN75LVDS389 HIGH-SPEED DIFFERENTIAL LINE DRIVERS

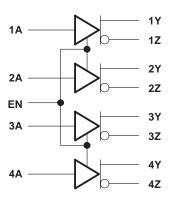
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description (continued)

The drivers are enabled in groups of four and are designated as banks A, B, C, and D. When disabled, the driver outputs are a high impedance. Each driver input (A) and enable (EN) have an internal pulldown that will drive the input to a low level when open circuited.

The SN65LVDS387 and SN65LVDS389 are characterized for operation from -40°C to 85°C. The SN75LVDS387 and SN75LVDS389 are characterized for operation from 0°C to 70°C.

logic diagram (positive logic)



(1/4 of 'LVDS387 or 1/2 of 'LVDS389 shown)

AVAILABLE OPTIONS

PART NUMBER†	TEMPERATURE RANGE	NO. OF DRIVERS	BUS-PIN ESD
SN65LVDS387DGG	–40°C to 85°C	16	12 kV
SN75LVDS387DGG	0°C to 70°C	16	4 kV
SN65LVDS389DBT	–40°C to 85°C	8	12 kV
SN75LVDS389DBT	0°C to 70°C	8	4 kV

[†] This package is available taped and reeled. To order this packaging option, add an R suffix to the part number (e.g., SN65LVDS387DGGR).

DRIVER FUNCTION TABLE

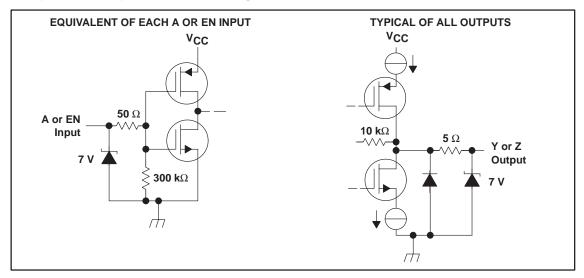
INPUT	ENABLE	OUTPUTS		
Α	EN	Υ	Z	
Н	Н	Н	L	
L	Н	L	Н	
Х	L	Z	Z	
OPEN	Н	L	Н	

H = high-level, L = low-level, X = irrelevant,

Z = high-impedance (off)



equivalent input and output schematic diagrams



absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage range, V _{CC}	0.5 V to 4 V
Input voltage range: Inputs	0.5 V to 6 V
Y or Z	0.5 V to 4 V
Electrostatic discharge: SN65' (Y, Z, and GND)	Class 3, A:12 kV, B: 500 V
SN65' (All pins)	Class 3, A: 4 kV, B:400 V
SN75' (Y, Z, and GND)	Class 3, A:4 kV, B: 400 V
SN75' (All pins)	Class 2, A: 2 kV, B:200 V
Continuous power dissipation	(see Dissipation Rating Table)
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 in) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C	DERATING FACTOR [‡] $A \le 25^{\circ}C$ $ABOVE T_{A} = 25^{\circ}C$ $POWER RATING$ PC		T _A = 85°C POWER RATING
DBT	1071 mW	8.5 mW/°C	688 mW	556 mW
DGG	2094 mW	16.7 mW/°C	1342 mW	1089 mW

[‡] This is the inverse of the junction-to-ambient thermal resistance when board-mounted (low-k) and with no air flow.

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}		3	3.3	3.6	V
High-level input voltage, V _{IH}		2			V
Low-level input voltage, V _{IL}				0.8	V
Operating free-air temperature, T _Δ	SN75'	0		70	°C
Operating nee-all temperature, 14	SN65'	-40		85	°C



NOTES: 1. All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

^{2.} Tested in accordance with MIL-STD-883C Method 3015.7.

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electrical characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CO	TEST CONDITIONS		TYP [†]	MAX	UNIT
IVODI	Differential output voltage magnitude	P 100 O		247	340	454	
Δ V _{OD}	Change in differential output voltage magnitude between logic states	$R_L = 100 \Omega_s$, See Figure 1 and 2		-50		50	mV
Voc(ss)	Steady-state common-mode output voltage			1.125		1.375	V
ΔV _{OC} (SS)	Change in steady-state common-mode output voltage between logic states	See 3		-50		50	mV
V _{OC(PP)}	Peak-to-peak common-mode output voltage]			50	150	mV
		'LVDS387	Enabled,		85	95	
I _{CC}	Supply current	'LVDS389	$R_L = 100 \Omega$, $V_{IN} = 0.8 \text{ V or 2 V}$		50	70	mA
.00		'LVDS387	Disabled,		0.5	1.5	
		'LVDS389	Λ IV = 0 Λ or Λ CC	0.5		1.5	1
lіН	High-level input current	V _{IH} = 2 V			3	20	μΑ
I _I L	Low-level input current	V _{IL} = 0.8 V			2	10	μΑ
la a	Short-circuit output current	V_{OY} or $V_{OZ} = 0$ V				±24	mA
los	Short-circuit output current	V _{OD} = 0 V				±12	mA
loz	High-impedance output current	VO = 0 V or VCC				±1	μΑ
IO(OFF)	Power-off output current	$V_{CC} = 1.5 V,$	V _O = 2.4 V			±1	μΑ
CIN	Input capacitance	$V_I = 0.4 \sin (4E6\pi t) + 0.5 V$			5		pF
co	Output capacitance	V _I = 0.4 sin (4E6πt) + Disabled	0.5 V,		9.4		pF

[†] All typical values are at 25°C and with a 3.3 V supply.

switching characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP [†]	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output		0.9	1.7	2.9	ns
tPHL	Propagation delay time, high-to-low-level output		0.9	1.6	2.9	ns
t _r	Differential output signal rise time	$R_1 = 100 \Omega$	0.4	0.8	1	ns
tf	Differential output signal fall time	$C_{L} = 10 \text{ pF},$	0.4	0.8	1	ns
tsk(p)	Pulse skew (tpHL - tpLH)	See Figure 4		150	500	ps
t _{sk(o)}	Output skew [‡]			80	150	ps
tsk(pp)	Part-to-part skew§				1.5	ns
^t PZH	Propagation delay time, high-impedance-to-high-level output			6.4	15	ns
tpzL	Propagation delay time, high-impedance-to-low-level output	See Figure 5		5.9	15	ns
tPHZ	Propagation delay time, high-level-to-high-impedance output	See Figure 5		3.5	15	ns
^t PLZ	Propagation delay time, low-level-to-high-impedance output			4.5	15	ns

[†] All typical values are at 25°C and with a 3.3 V supply.



[‡] t_{SK(0)} is the magnitude of the time difference between the tpLH or tpHL of all drivers of a single device with all of their inputs connected together. § t_{SK(0)}p) is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

PARAMETER MEASUREMENT INFORMATION

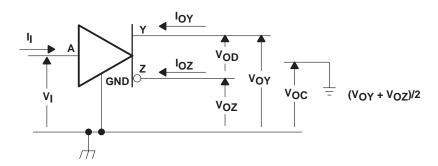


Figure 1. Voltage and Current Definitions

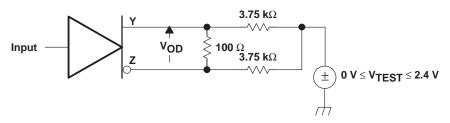
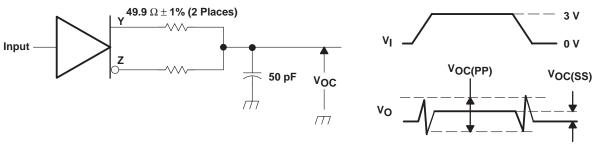
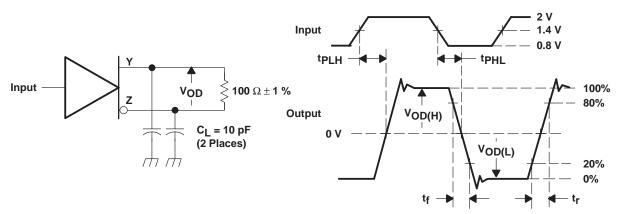


Figure 2. VOD Test Circuit



NOTE: All input pulses are supplied by a generator having the following characteristics: t_r or t_f ≤ 1 ns, Pulse Repetition Rate (PRR) = 0.5 Mpps, Pulse width = 500 ± 10 ns . C_L includes instrumentation and fixture capacitance within 0,06 m of the D.U.T. The measurement of V_{OC(PP)} is made on test equipment with a −3 dB bandwidth of at least 300 MHz.

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

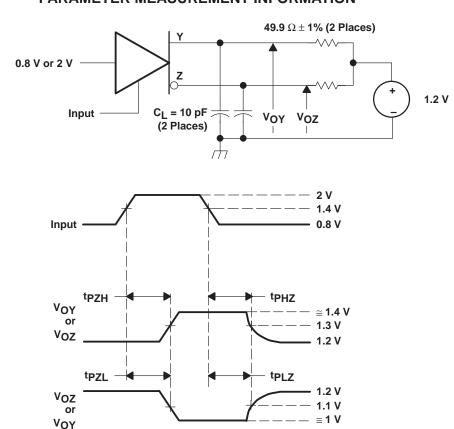


NOTE: All input pulses are supplied by a generator having the following characteristics: t_{Γ} or $t_{\Gamma} \le 1$ ns, Pulse Repetition Rate (PRR) = 50 Mpps, Pulse width = 10 ± 0.2 ns . C_{Γ} includes instrumentation and fixture capacitance within 0,06 m of the D.U.T.

Figure 4. Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal



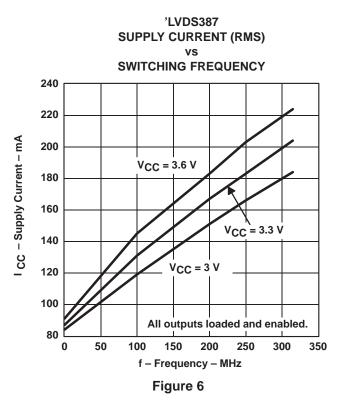
PARAMETER MEASUREMENT INFORMATION

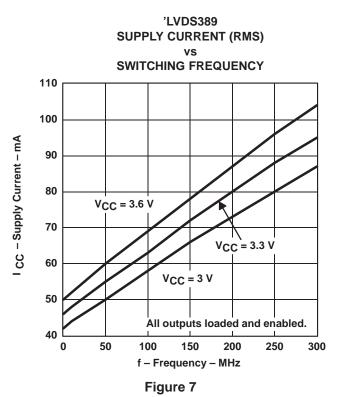


NOTE: All input pulses are supplied by a generator having the following characteristics: t_T or $t_f \le 1$ ns, Pulse Repetition Rate (PRR) = 0.5 Mpps, Pulse width = 500 ± 10 ns . C_L includes instrumentation and fixture capacitance within 0,06 m of the D.U.T.

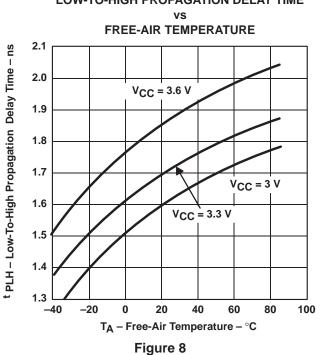
Figure 5. Enable and Disable Time Circuit and Definitions

TYPICAL CHARACTERISTICS

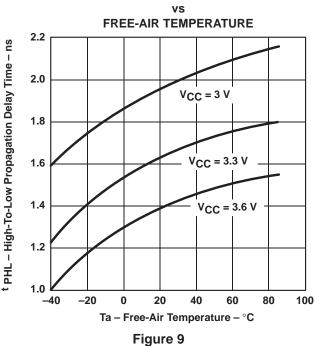




LOW-TO-HIGH PROPAGATION DELAY TIME

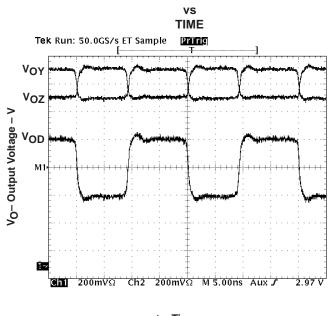


HIGH-TO-LOW PROPAGATION DELAY TIME



TYPICAL CHARACTERISTICS

OUTPUT VOLTAGE



t – Time – ns

Figure 10



APPLICATION INFORMATION

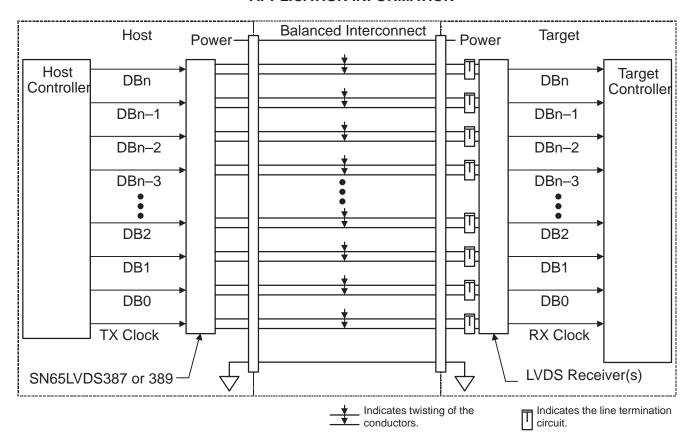


Figure 11. Typical Application Schematic

Signaling Rate vs Distance

The ultimate data transfer rate over a given cable or trace length involves many variables. Starting with the capabilities of this LVDS driver to reproduce a data pulse as short as 1.6 ns (a 630 Mbps signaling rate) with less than 500 ps of pulse distortion, any degradation of this pulse by the transmission media will necessarily reduce the timing margin at the receiving end of the data link.

The timing uncertainty induced by the transmission media is commonly referred to as jitter and comes from numerous sources. The characteristics of a particular transmission media can be quantified by using an eyepattern measurement such as shown in Figure 12, which shows about 340 ps of jitter or 20% of the data pulse width.

APPLICATION INFORMATION

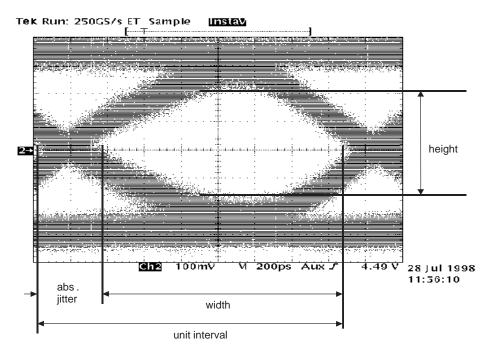


Figure 12. Typical LVDS Eyepattern

A generally accepted range of jitter at the receiver inputs that allows data recovery is 5% to 20% of the unit interval (data pulse width). Table 1 shows the signaling rate achieved on various cables and lengths at a 5% eyepattern jitter with a typical LVDS driver.

Table 1. Signaling Rates for Various Cables for 5% Eyepattern Jitter

LENGTH	CABLE [†]						
(m)	A (Mbps)	B (Mbps)	C (Mbps)	D (Mbps)	E (Mbps)	F (Mbps)	
1	240	200	240	270	180	230	
5	205	210	230	250	215	230	
10	180	150	195	200	145	180	

TCable A: CAT 3, specified up to 16 MHz, no shield, outside conductor diameter (Ø) 0.52 mm

Cable B: CAT 5, specified up to 100 MHz, no shield, \varnothing 0.52 mm

Cable C: CAT 5, specified up to 100 MHz, taped over all shield, \varnothing 0.52 mm

Cable D: CAT 5 (exceeding CAT 5), specified up to 300 MHz, braided over all shield plus taped individual shield for any pair, Ø 0.64 mm (AWG22)

Cable E: CAT 5 (exceeding CAT 5), specified up to 350 MHz, \varnothing 0.64 mm (AWG22), no shield

Cable F: CAT 5 (exceeding CAT 5), specified up to 350 MHz, "self-shielded", Ø 0.64 mm (AWG22)

During synchronous parallel transfers, skew between the data and clock lines will also reduce the timing margin. This must be accounted for in the system timing budget. Fortunately, the low output skew of this LVDS driver will generally be a small portion of this budget.

other LVDS products

For other products and applications notes in the LVDS and LVDM product families visit our Web site at http://www.ti.com/sc/datatran.



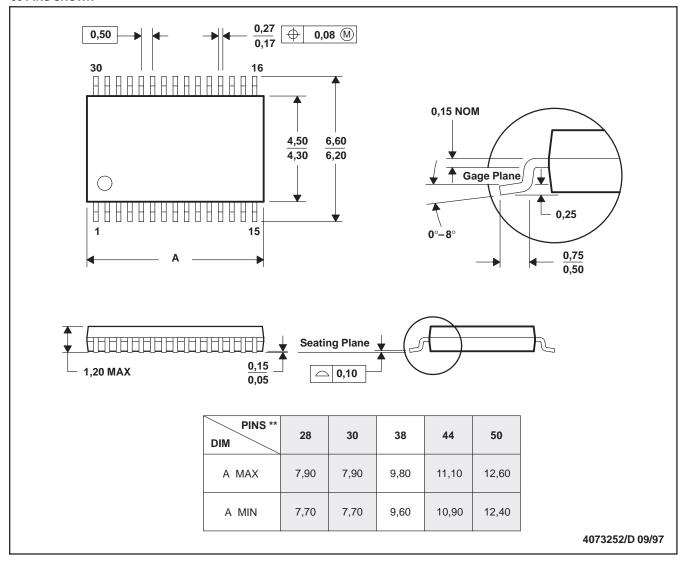
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MECHANICAL DATA

DBT (R-PDSO-G**)

30 PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion.

D. Falls within JEDEC MO-153

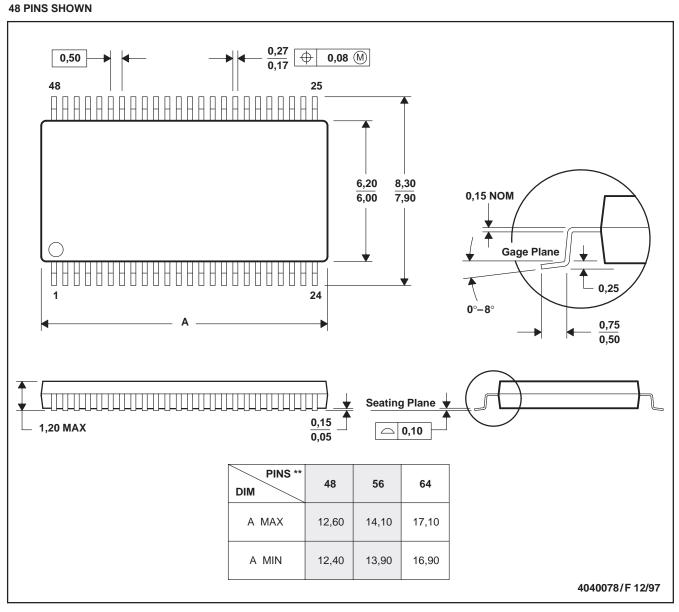
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MECHANICAL DATA

DGG (R-PDSO-G**)

, ,

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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